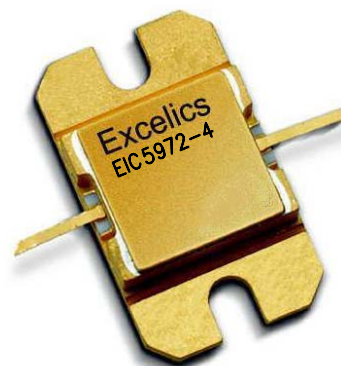


FEATURES

- 5.90– 7.20GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.5 dBm Output Power at 1dB Compression
- 9.0 dB Power Gain at 1dB Compression
- 32% Power Added Efficiency
- -46 dBc IM3 at PO = 29.5 dBm SCL
- Hermetic Metal Flange Package
- 100% Tested for DC, RF, and R_{TH}



ELECTRICAL CHARACTERISTICS (T_a = 25°C)



Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 1100mA f = 5.90-7.20GHz	35.5	36.5		dBm
G_{1dB}	Gain at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 1100mA f = 5.90-7.20GHz	8.0	9.0		dB
ΔG	Gain Flatness V _{DS} = 10 V, I _{DSQ} ≈ 1100mA f = 5.90-7.20GHz			±0.8	dB
PAE	Power Added Efficiency at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 1100mA f = 5.90-7.20GHz		32		%
I_{d1dB}	Drain Current at 1dB Compression f = 5.90-7.20GHz		1200	1400	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 29.5 dBm S.C.L. ² V _{DS} = 10 V, I _{DSQ} ≈ 65% IDSS f = 7.20GHz	-43	-46		dBc
I_{DSS}	Saturated Drain Current V _{DS} = 3 V, V _{GS} = 0 V		2000	2500	mA
V_P	Pinch-off Voltage V _{DS} = 3 V, I _{DS} = 20 mA		-2.5	-4.0	V
R_{TH}	Thermal Resistance ³		5.5	6.0	°C/W

Note: 1) Tested with 100 Ohm gate resistor. 2) S.C.L. = Single Carrier Level. 3) Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{DS}	Drain-Source Voltage	15	10V
V_{GS}	Gate-Source Voltage	-5	-4V
I_{gsf}	Forward Gate Current	43.2mA	14.4mA
I_{gsr}	Reverse Gate Current	-7.2mA	-2.4mA
P_{in}	Input Power	35.5dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175 °C	175 °C
T_{stg}	Storage Temperature	-65 to +175 °C	-65 to +175 °C
P_t	Total Power Dissipation	25W	25W

Note: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.

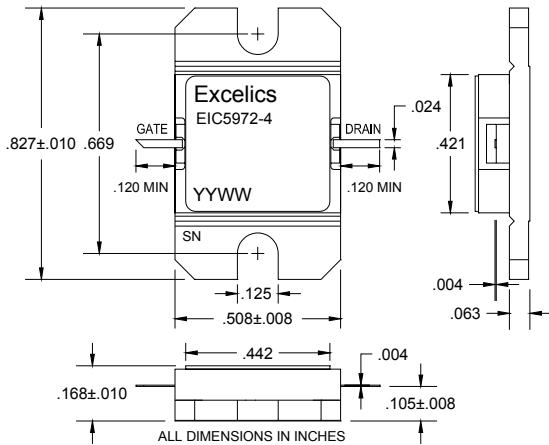
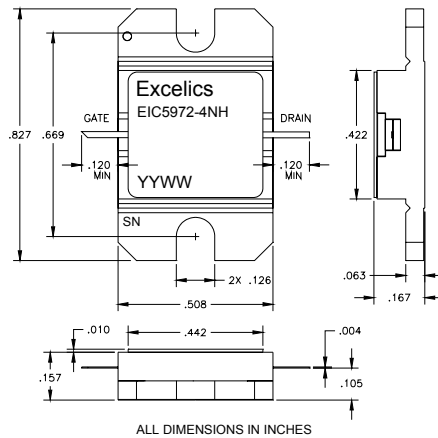
Specifications are subject to change without notice.

UPDATED 12/07/2007

5.90-7.20 GHz 4-Watt Internally Matched Power FET

PACKAGES OUTLINE

 Dimensions in inches, Tolerance $\pm .005$ unless otherwise specified

EIC5972-4 (Hermetic)

EIC5972-4NH (Non-Hermetic)

Caution! ESD sensitive device.

Caution! ESD sensitive device.

ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC5972-4	Hermetic	Industrial	5.90-7.20GHz	35.5	-43
EIC5972-4NH	Non-Hermetic	Industrial	5.90-7.20GHz	35.5	-43

Notes: 1. Contact factory for military and hi-rel grades.
 2. Exact test conditions are specified in "Electrical Characteristics" table.

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness

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 Revised December 2007